2SK3030

Silicon N-channel power MOSFET

■ Features

- Avalanche energy capability guaranteed
- High-speed switching
- Low ON resistance Ron
- No secondary breakdown
- Low-voltage drive
- High electrostatic energy capability

■ Applications

- Non-contact relay
- Solenoid drive
- Motor drive
- Control equipment
- Switching mode regulator

■ Absolute Maximum Ratings $T_C = 25$ °C

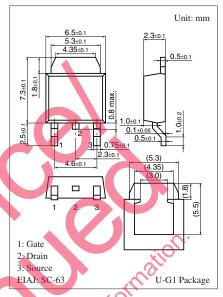
Parameter	Symbol	Rating	Unit	
Drain-source surrender voltage	V _{DSS}	100	V	
Gate-source surrender voltage	V_{GSS}	±20	V	
Drain current	I_{D}	±8	A	
Peak drain current	I_{DP}	±24	A	
Avalanche energy capability *	EAS	3.2	mJ	
Power dissipation	$P_{\rm D}$	15	W	
$T_a = 25^{\circ}C$		1		
Channel temperature	T_{ch}	150	°C	
Storage temperature	T _{stg}	-55 to +150	°C	

Note) *: L = 0.1 mH, $I_L = 8 \text{ A}$, 1 pulse

■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

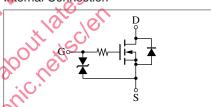
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Drain-source surrender voltage	V _{DSS}	$I_D = 1 \text{ mA}, V_{GS} = 0$	100			V
Drain-source cutoff current	I_{DSS}	$V_{DS} = 80$ V, $V_{GS} = 0$			10	μΑ
Gate-source cutoff current	I_{GSS}	$V_{GS} = \pm 20 \text{ V}, V_{DS} = 0$			±10	μΑ
Gate threshold voltage	V_{th}	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	1.0		2.5	V
Forward transfer admittance	Yfs	$V_{\rm DS} = 10 \text{V}, I_{\rm D} = 4 \text{A}$	2	4		S
Drain-source ON resistance	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 4 \text{ A}$		0.15	0.23	Ω
	R _{DS(on)2}	$V_{GS} = 4 \text{ V}, I_D = 4 \text{ A}$		0.18	0.26	
Diode forward voltage	V_{DSF}	$I_{DR} = 8 A, V_{GS} = 0$			-1.4	V
Short-circuit forward transfer capacitance (Common source)	C _{iss}	$V_{DS} = 10 \text{ V}, V_{GS} = 0, f = 1 \text{ MHz}$		290		pF
Short-circuit output capacitance (Common source)	C _{oss}			110		pF
Reverse transfer capacitance (Common source)	C _{rss}			30		pF
Turn-on delay time	t _{d(on)}	$V_{DD} = 30 \text{ V}, I_D = 4 \text{ A}, R_L = 7.5 \Omega$		15		ns
Rise time	t _r	$V_{GS} = 10 \text{ V}$		40		ns
Fall time	$t_{\rm f}$			200		ns
Turn-off delay time	t _{d(off)}			860		ns
Thermal resistance (ch-c)	R _{th(ch-c)}				8.33	°C/W
Thermal resistance (ch-a)	R _{th(ch-a)}				125	°C/W

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.



Marking Symbol: K3030

Internal Connection



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